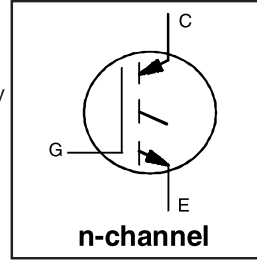


IRGB30B60KPbF
IRGS30B60KPbF
IRGSL30B60KPbF

INSULATED GATE BIPOLAR TRANSISTOR

Features

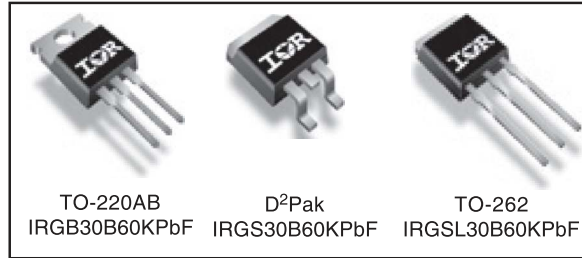
- Low VCE (on) Non Punch Through IGBT Technology
- 10µs Short Circuit Capability
- Square RBSOA
- Positive VCE (on) Temperature Coefficient
- Maximum Junction Temperature rated at 175°C
- Lead-Free



$V_{CES} = 600V$
 $I_C = 50A, T_C=100^\circ C$
at $T_J=175^\circ C$
 $t_{sc} > 10\mu s, T_J=150^\circ C$
 $V_{CE(on)} \text{ typ.} = 1.95V$

Benefits

- Benchmark Efficiency for Motor Control
- Rugged Transient Performance
- Low EMI
- Excellent Current Sharing in Parallel Operation



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	78 ^⑤	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	50	
I_{CM}	Pulse Collector Current (Ref.Fig.C.T.5)	120	
I_{LM}	Clamped Inductive Load current ①	120	
V_{ISOL}	RMS Isolation Voltage, Terminal to Case, t=1 min.	2500	V
V_{GE}	Gate-to-Emitter Voltage	±20	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	370	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	180	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf-in (1.1 N-m)	

Thermal / Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case- IGBT	—	—	0.41*	°C/W
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount ②	—	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, Steady State)③	—	—	40	
Wt	Weight	—	1.44	—	g

* $R_{\theta JC}$ (end of life) = 0.65°C/W. This is the maximum measured value after 1000 temperature cycles from -55 to 150°C and is accounted for by the physical wearout of the die attach medium.

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V _{GE} = 0V, I _C = 500μA	
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	0.40	—	V/°C	V _{GE} = 0V, I _C = 1mA (25°C-150°C)	
V _{CE(on)}	Collector-to-Emitter Voltage	—	1.95	2.35	V	I _C = 30A, V _{GE} = 15V, T _J = 25°C	5,6,7
		—	2.40	2.75		I _C = 30A, V _{GE} = 15V, T _J = 150°C	8,9,10
		—	2.6	2.95		I _C = 30A, V _{GE} = 15V, T _J = 175°C	
V _{GE(th)}	Gate Threshold Voltage	3.5	4.5	5.5	V	V _{CE} = V _{GE} , I _C = 250μA	8,9,10
ΔV _{GE(th)} /ΔT _J	Threshold Voltage temp. coefficient	—	-10	—	mV/°C	V _{CE} = V _{GE} , I _C = 1.0mA (25°C-150°C)	11
g _{fe}	Forward Transconductance	—	18	—	S	V _{CE} = 50V, I _C = 50A, PW = 80μs	
I _{CES}	Zero Gate Voltage Collector Current	—	5.0	250	μA	V _{GE} = 0V, V _{CE} = 600V	
		—	1000	2000		V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C	
		—	1830	3000		V _{GE} = 0V, V _{CE} = 600V, T _J = 175°C	
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V, V _{CE} = 0V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
Q _g	Total Gate Charge (turn-on)	—	102	153	nC	I _C = 30A	17
Q _{ge}	Gate-to-Emitter Charge (turn-on)	—	14	21		V _{CC} = 400V	CT1
Q _{gc}	Gate-to-Collector Charge (turn-on)	—	44	66		V _{GE} = 15V	
E _{on}	Turn-On Switching Loss	—	350	620	μJ	I _C = 30A, V _{CC} = 400V	CT4
E _{off}	Turn-Off Switching Loss	—	825	955		V _{GE} = 15V, R _G = 10Ω, L = 200μH	
E _{tot}	Total Switching Loss	—	1175	1575		T _J = 25°C ④	
t _{d(on)}	Turn-On delay time	—	46	60	ns	I _C = 30A, V _{CC} = 400V	CT4
t _r	Rise time	—	28	39		V _{GE} = 15V, R _G = 10Ω, L = 200μH	
t _{d(off)}	Turn-Off delay time	—	185	200		T _J = 25°C	
t _f	Fall time	—	31	40			
E _{on}	Turn-On Switching Loss	—	635	1085		I _C = 30A, V _{CC} = 400V	
E _{off}	Turn-Off Switching Loss	—	1150	1350	μJ	V _{GE} = 15V, R _G = 10Ω, L = 200μH	12,14
E _{tot}	Total Switching Loss	—	1785	2435		T _J = 150°C ④	WF1,WF2
t _{d(on)}	Turn-On delay time	—	46	60		I _C = 30A, V _{CC} = 400V	13,15
t _r	Rise time	—	28	39	ns	V _{GE} = 15V, R _G = 10Ω, L = 200μH	CT4
t _{d(off)}	Turn-Off delay time	—	205	235		T _J = 150°C	WF1
t _f	Fall time	—	32	42			WF2
L _E	Internal Emitter Inductance	—	7.5	—		nH	Measured 5mm from package
C _{ies}	Input Capacitance	—	1750	2500	pF	V _{GE} = 0V	16
C _{oes}	Output Capacitance	—	160	255		V _{CC} = 30V	
C _{res}	Reverse Transfer Capacitance	—	60	90		f = 1.0MHz	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T _J = 150°C, I _C = 120A, V _p = 600V V _{CC} =500V, V _{GE} = +15V to 0V, R _G = 10Ω	4 CT2
SCSOA	Short Circuit Safe Operating Area	10	—	—	μs	T _J = 150°C, V _p = 600V, R _G = 10Ω V _{CC} =360V, V _{GE} = +15V to 0V	CT3 WF3
I _{SC (Peak)}	Peak Short Circuit Collector Current	—	200	—	A		WF3

Note ① to ⑤ are on page 13

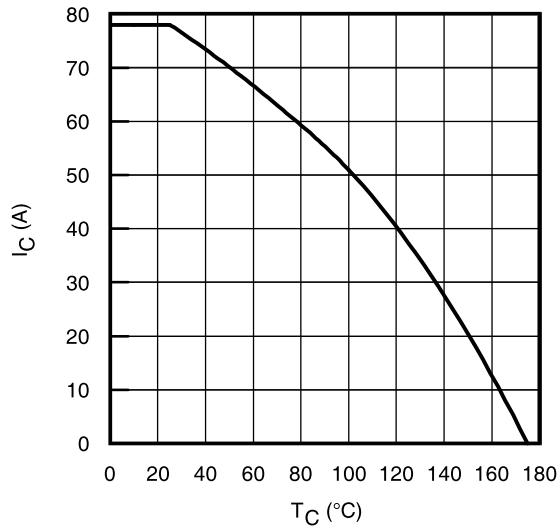


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

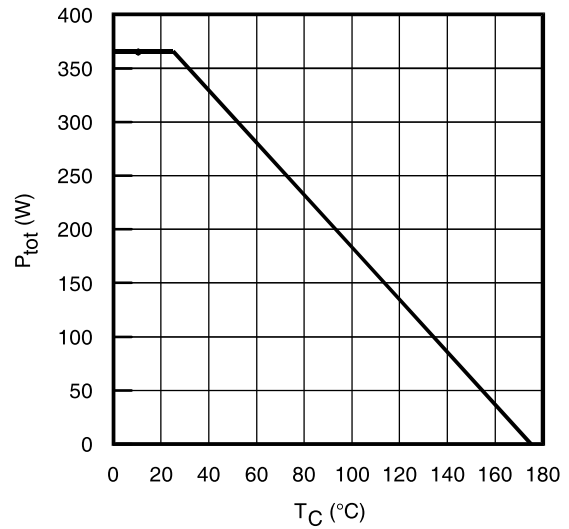


Fig. 2 - Power Dissipation vs. Case Temperature

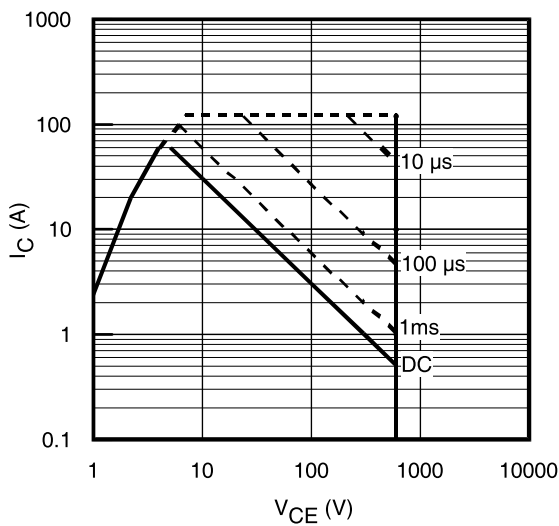


Fig. 3 - Forward SOA
 $T_C = 25^{\circ}C$; $T_J \leq 150^{\circ}C$

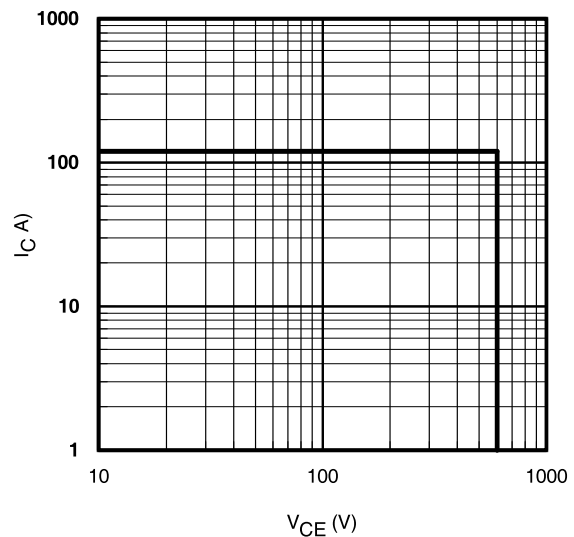


Fig. 4 - Reverse Bias SOA
 $T_J = 150^{\circ}C$; $V_{GE} = 15V$

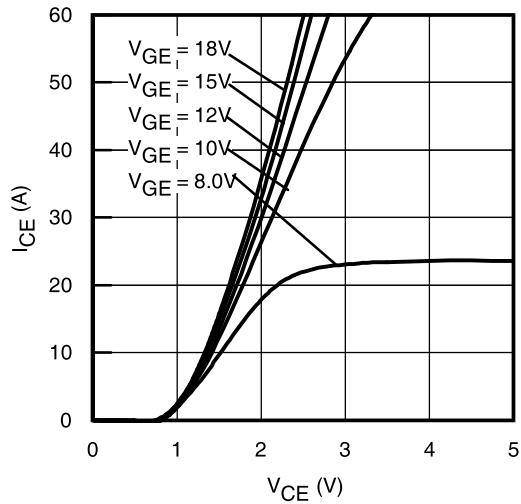


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p = 80\mu\text{s}$

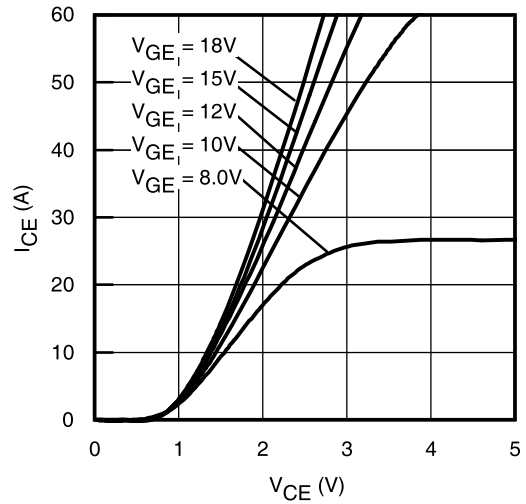


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 80\mu\text{s}$

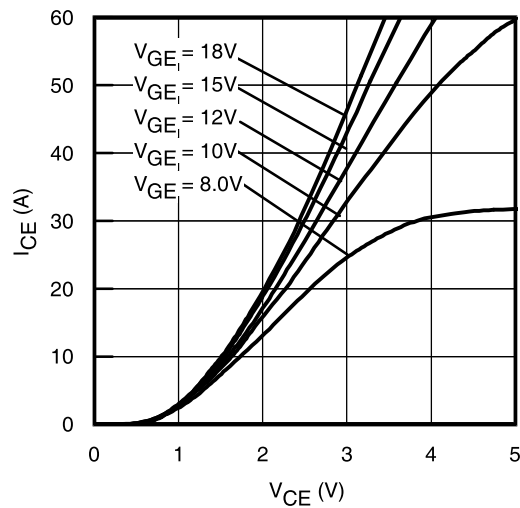


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 150^\circ\text{C}$; $t_p = 80\mu\text{s}$

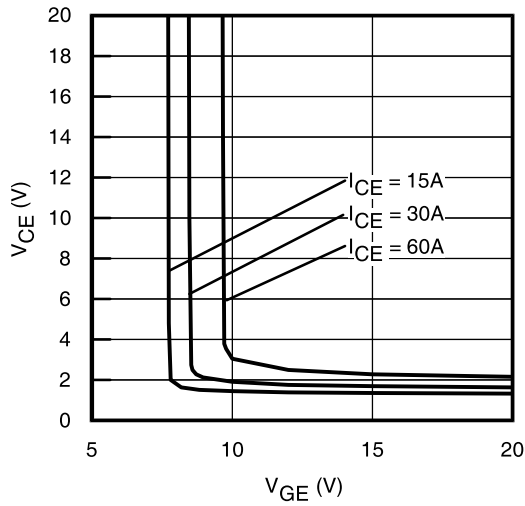


Fig. 8 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

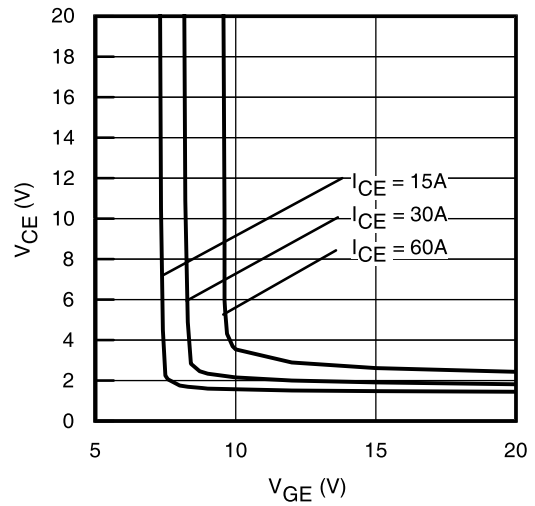


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

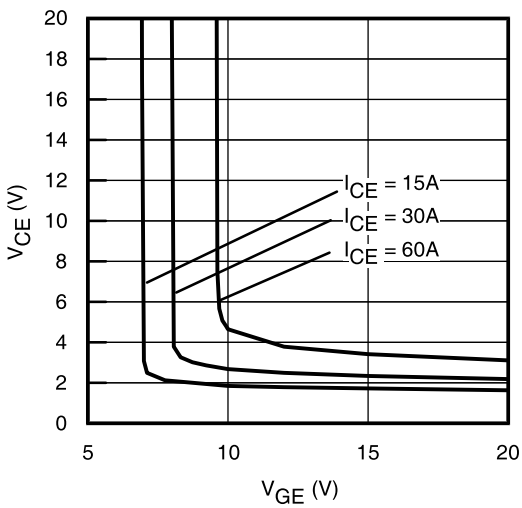


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 150^\circ\text{C}$

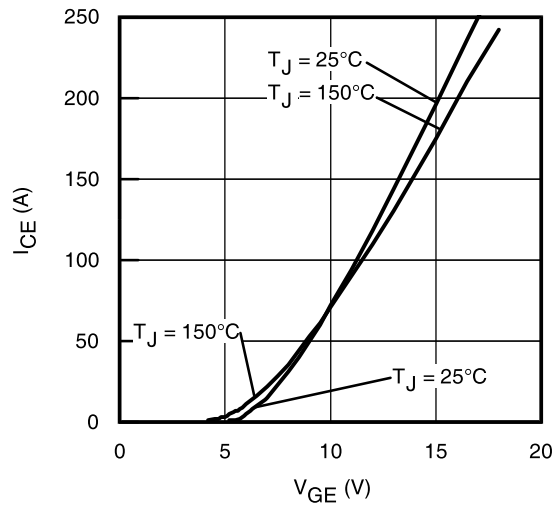


Fig. 11 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 10\mu\text{s}$

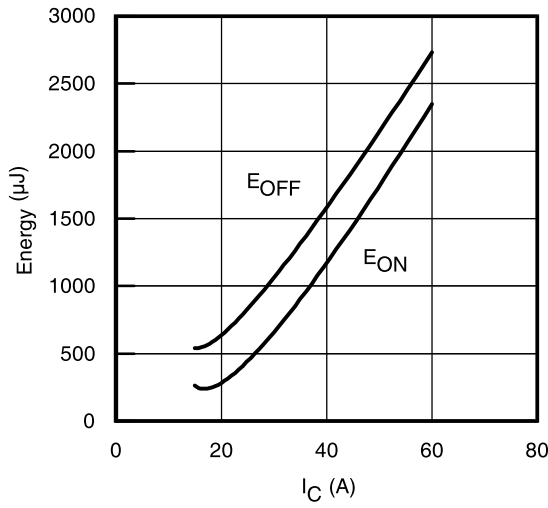


Fig. 12 - Typ. Energy Loss vs. I_C
 $T_J = 150^\circ\text{C}$; $L=200\mu\text{H}$; $V_{CE}= 400\text{V}$,
 $R_G= 10\Omega$; $V_{GE}= 15\text{V}$

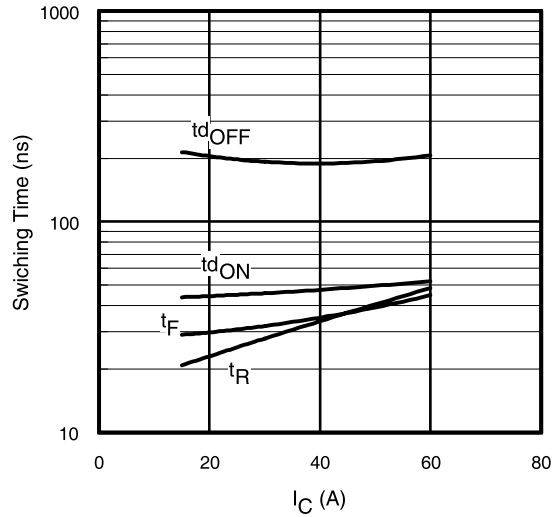


Fig. 13 - Typ. Switching Time vs. I_C
 $T_J = 150^\circ\text{C}$; $L=200\mu\text{H}$; $V_{CE}= 400\text{V}$
 $R_G= 10\Omega$; $V_{GE}= 15\text{V}$

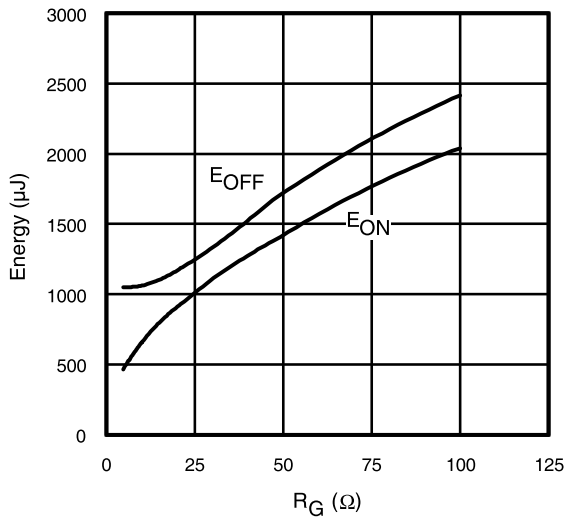


Fig. 14 - Typ. Energy Loss vs. R_G
 $T_J = 150^\circ\text{C}$; $L=200\mu\text{H}$; $V_{CE}= 400\text{V}$
 $I_{CE}= 30\text{A}$; $V_{GE}= 15\text{V}$

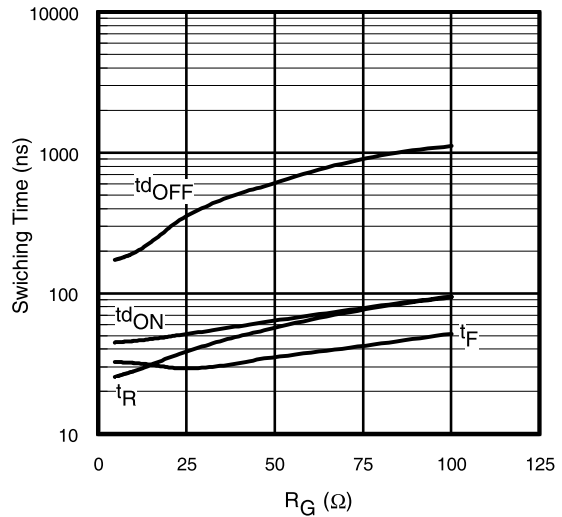


Fig. 15 - Typ. Switching Time vs. R_G
 $T_J = 150^\circ\text{C}$; $L=200\mu\text{H}$; $V_{CE}= 400\text{V}$
 $I_{CE}= 30\text{A}$; $V_{GE}= 15\text{V}$

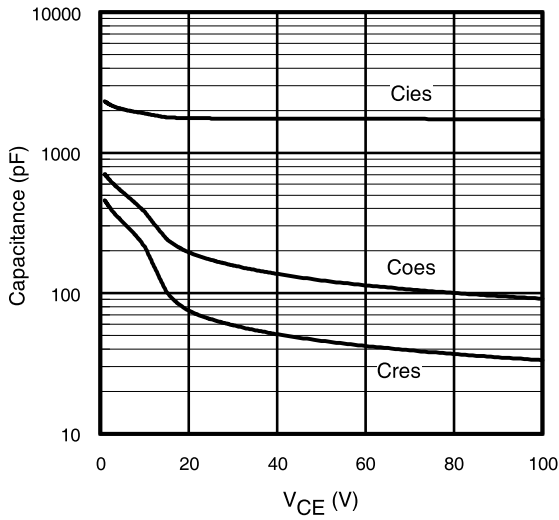


Fig. 16- Typ. Capacitance vs. V_{CE}
V_{GE} = 0V; f = 1MHz

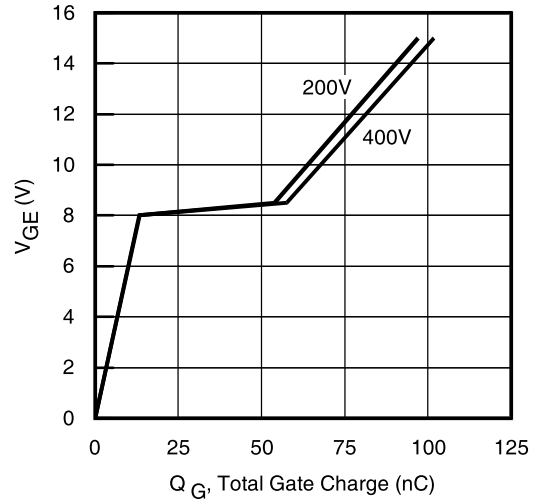


Fig. 17 - Typical Gate Charge vs. V_{GE}
I_{CE} = 30A; L = 600μH

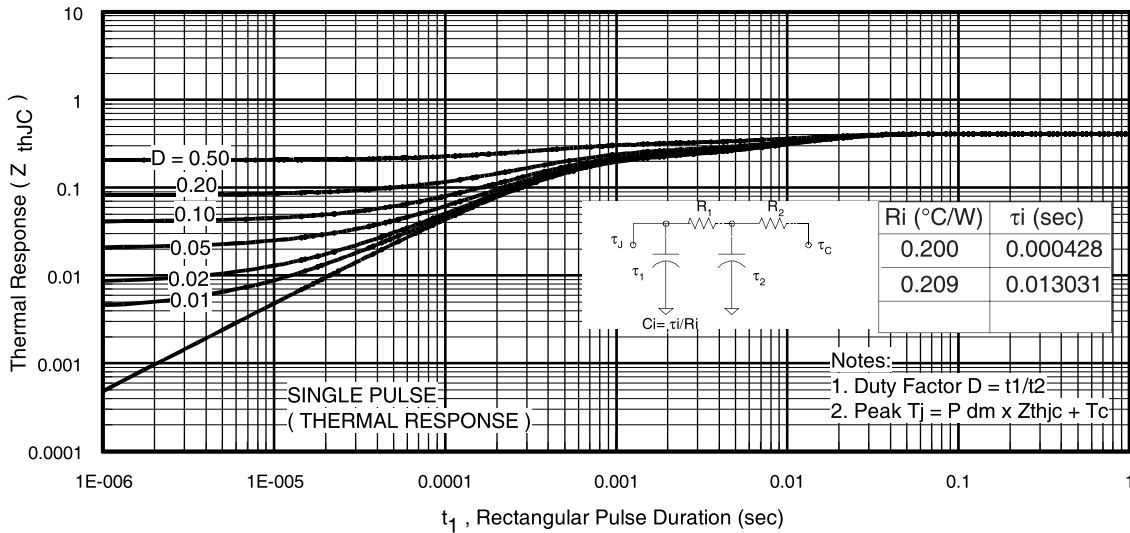


Fig 18. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

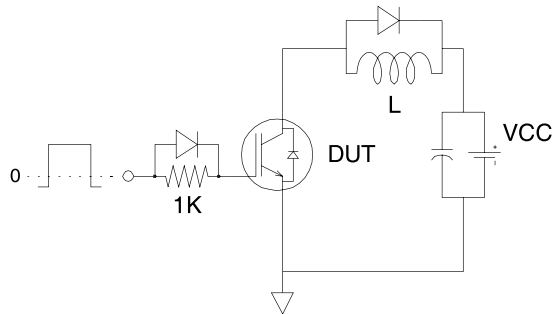


Fig.C.T.1 - Gate Charge Circuit (turn-off)

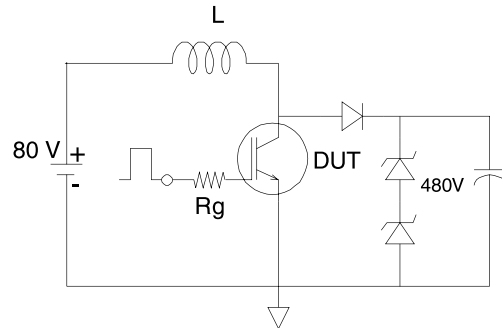


Fig.C.T.2 - RBSOA Circuit

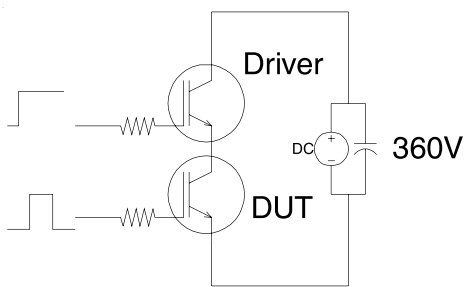


Fig.C.T.3 - S.C.SOA Circuit

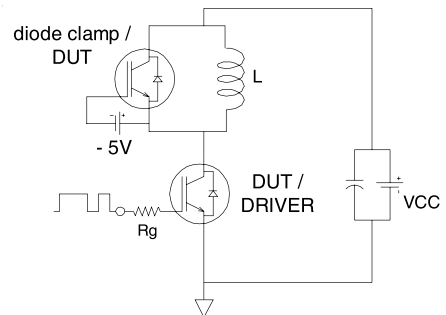


Fig.C.T.4 - Switching Loss Circuit

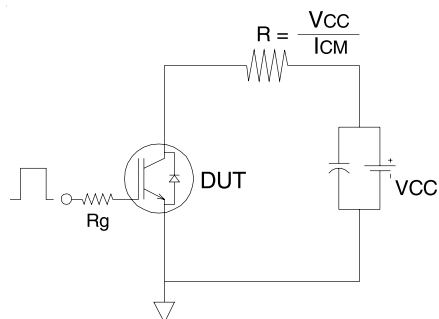


Fig.C.T.5 - Resistive Load Circuit

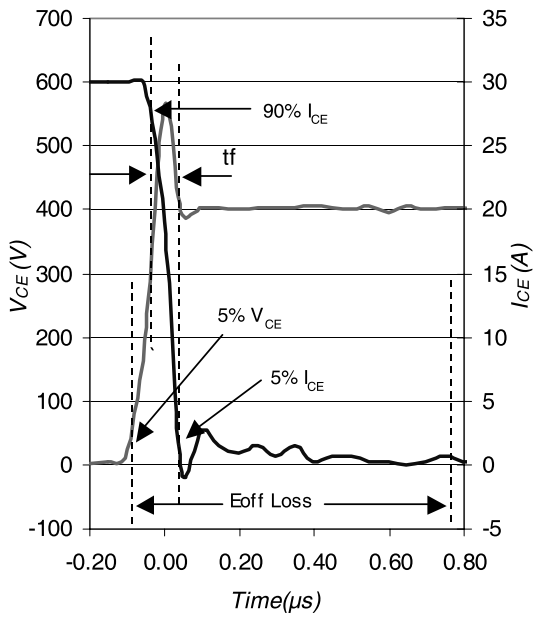


Fig. WF1- Typ. Turn-off Loss Waveform
 @ $T_J = 150^\circ\text{C}$ using Fig. CT.4

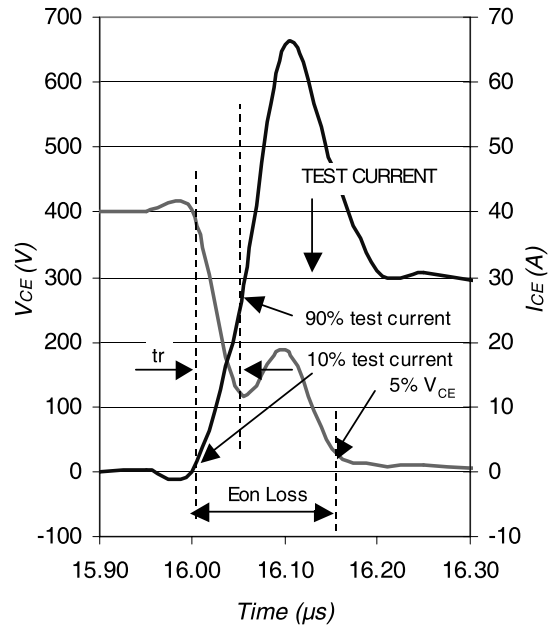


Fig. WF2- Typ. Turn-on Loss Waveform
 @ $T_J = 150^\circ\text{C}$ using Fig. CT.4

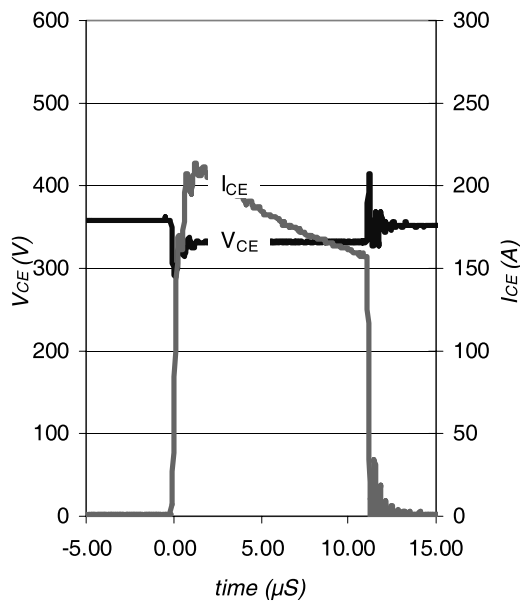
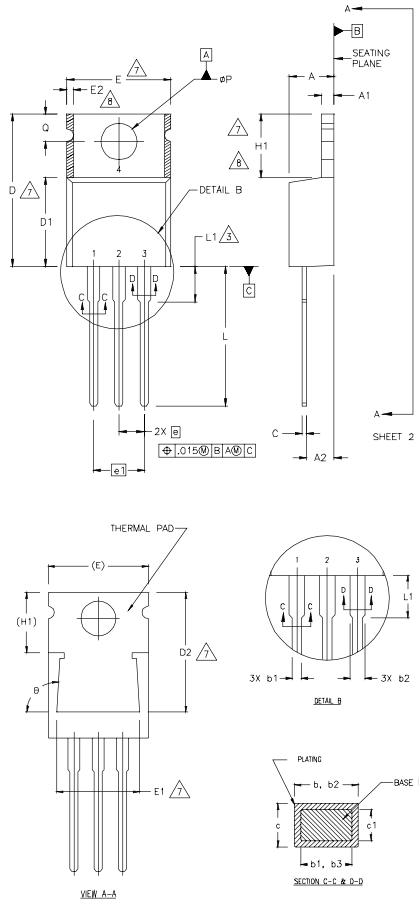


Fig. WF3- Typ. S.C Waveform
 @ $T_C = 150^\circ\text{C}$ using Fig. CT.3

IRGB/S/SL30B60KPbF

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
- 6 CONTROLLING DIMENSION : INCHES.
- 7 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULARITIES IRREGULARITIES ARE ALLOWED.

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

IGBTs - CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

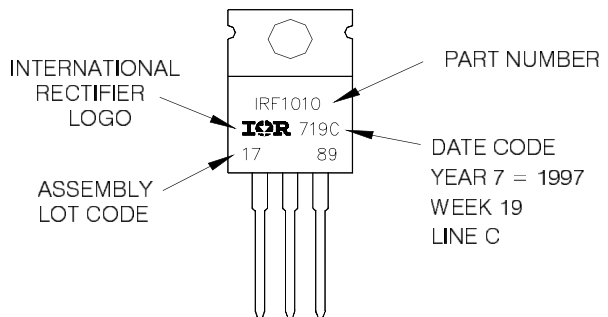
DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	5
b2	1.15	1.77	.045	.070	
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	12.19	12.88	.480	.507	7
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
e	2.54 BSC		.100 BSC		
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	-	6.35	-	.250	3
ØP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	
Ø	90°-93°		90°-93°		

TO-220AB Part Marking Information

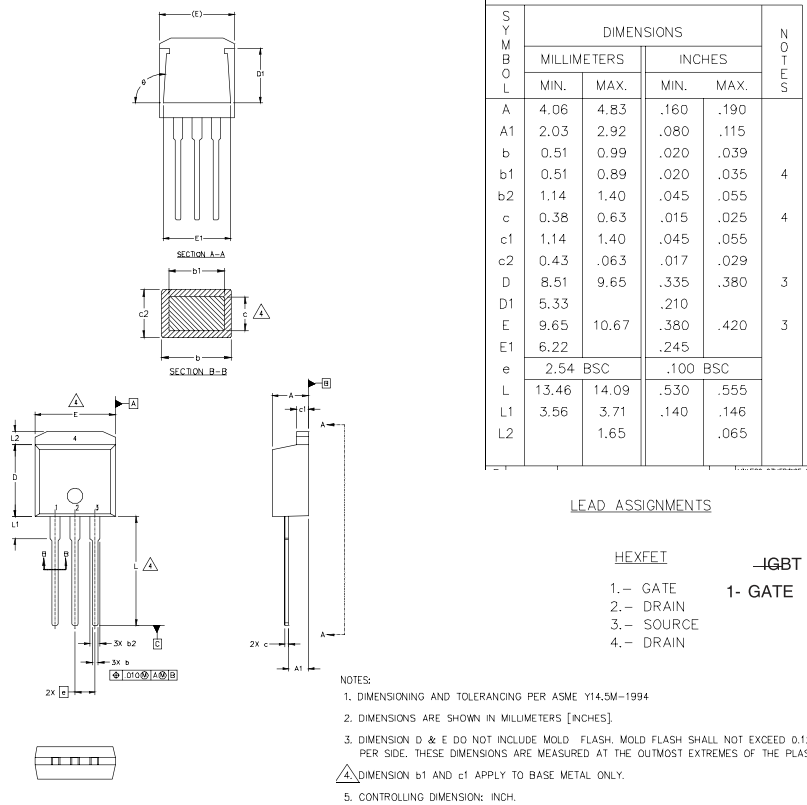
EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line position indicates "Lead-Free"



IRGB/S/SL30B60KPbF

TO-262 Package Outline

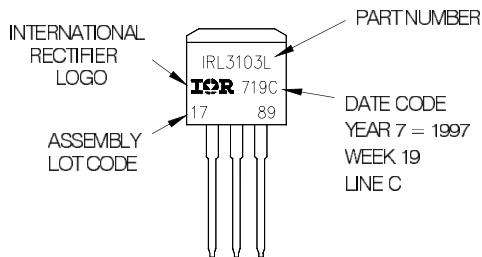
Dimensions are shown in millimeters (inches)



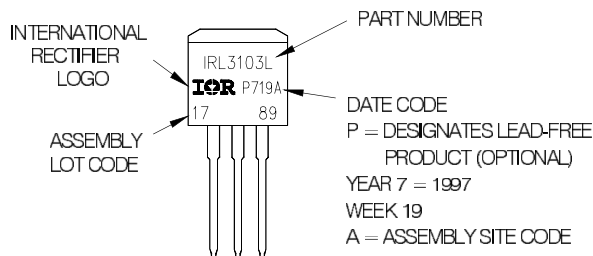
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
 LOT CODE 1789
 ASSEMBLED ON VWV 19, 1997
 IN THE ASSEMBLY LINE 'C'

Note: "P" in assembly line position indicates "Lead - Free"

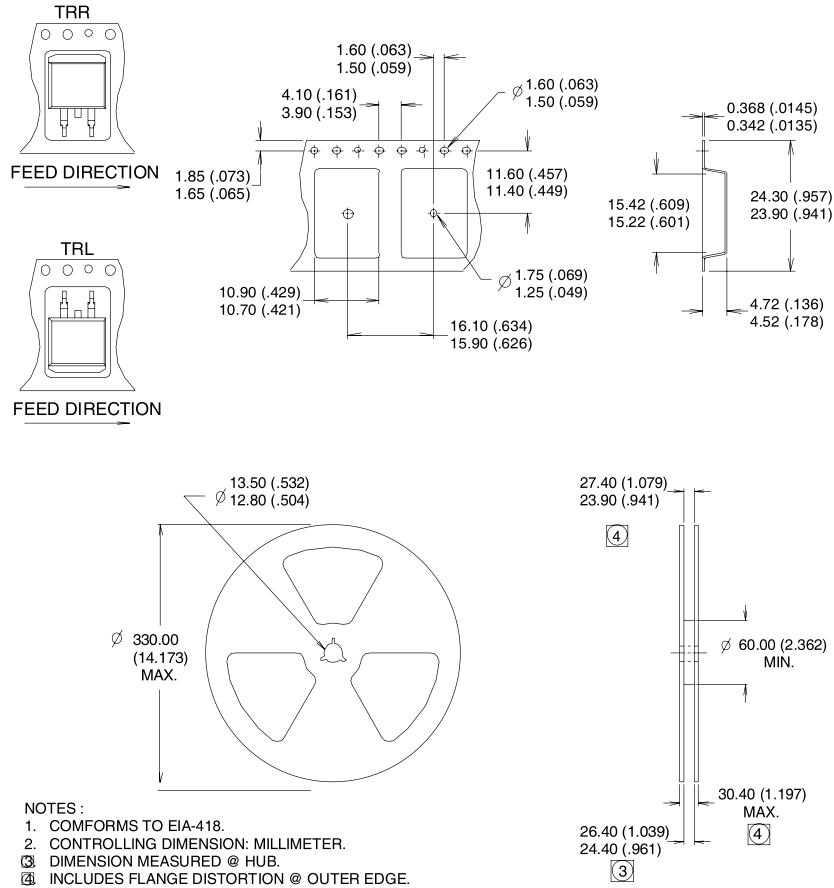


OR



D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Notes:

- ① $V_{CC} = 80\% (V_{CES})$, $V_{GE} = 20V$, $L = 28\mu H$, $R_G = 22\Omega$.
- ② This is only applied to TO-220AB package.
- ③ This is applied to D²Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.
- ④ Energy losses include "tail" and diode reverse recovery.
- ⑤ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

TO-220AB package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>